

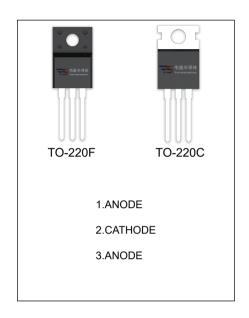
SBD20150CT SBDF20150CT SCHOTTKY BARRIER RECTIFIER

MAIN CHARACTERISTICS

| Io | 20 (2×10) A |
|----------------|------------------|
| V_{RRM} | 150 V |
| T _j | 150 ℃ |
| $V_{F(typ)}$ | 0.71V (@Tj=125℃) |

FEATURES

- Low Power Loss, High Efficiency
- Guard Ring Die Construction for Transient Protection
- High Current Capability and Low Forward Voltage Drop



MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

| Cumbal | Parameter | | SBD | |
|---------------------|--|----------|----------|------|
| Symbol | | | F20150CT | Unit |
| V _{RRM} | Peak repetitive reverse voltage | | | |
| V _{RWM} | Working peak reverse voltage | | 150 | |
| V _R | DC blocking voltage | | | |
| V _{R(RMS)} | RMS reverse voltage | 105 | | V |
| Io | Average rectified output current | 20 | | Α |
| I _{FSM} | Non-Repetitive peak forward surge current (8.3ms half sine wave) | 150 | | Α |
| R _{⊝Jc} | Thermal resistance from junction to case ,Tc=25℃ | 2.0 | 3.0 | °C/W |
| R _{OJA} | Thermal resistance from junction to ambient | 62.5 | | °C/W |
| T _j | Junction temperature | 150 | | °C |
| T _{stg} | Storage temperature | -55~+150 | | °C |

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

| Parameter | Symbol | Test conditions | | Min | Тур | Max | Unit |
|-----------------|-------------------|----------------------|----------|-----|------|------|------|
| Reverse voltage | V _(BR) | | | 150 | | | V |
| Reverse current | I _R | V _R =150V | Tj =25℃ | | 2.0 | 100 | uA |
| | | | Tj =125℃ | | 2.0 | | mA |
| Forward voltage | V _F | I _F =5A | Tj =25℃ | | 0.76 | | V |
| | | | Tj =125℃ | | 0.64 | | V |
| | | I _F =10A | Tj =25℃ | | 0.83 | 0.90 | V |
| | | | Tj =125℃ | | 0.71 | | V |

^{*}Pulse test: pulse width ≤300µs, duty cycle≤ 2.0%.



